



NPN Silicon Transistor

Descriptions

- General purpose amplifier
- High voltage application

Features

• High collector breakdown voltage :

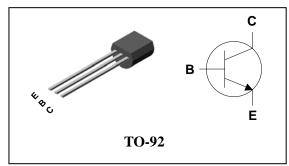
 $V_{CBO} = 180V, V_{CEO} = 160V$

• Low collector saturation voltage :

 $V_{CE(sat)} = 0.5V(MAX.)$

• Complementary pair with 2N5401

PIN Connection



Ordering Information

Type NO.	Marking	Package Code	
2N5551	2N5551	TO-92	

Absolute maximum ratings

(Ta=25°C)

Characteristic	Symbol	Ratings	Unit
Collector-Base voltage	V_{CBO}	180	V
Collector-Emitter voltage	$V_{\sf CEO}$	160	V
Emitter-Base voltage	V_{EBO}	6	V
Collector current	I _C	600	mA
Collector dissipation	P _C	625	mW
Junction temperature	Tj	150	°C
Storage temperature	T_{stg}	-55~150	°C

Electrical Characteristics

(Ta=25°C)

Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Collector-Base breakdown voltage	BV_CBO	$I_C = 100 \mu A, I_E = 0$	180	-	-	V
Collector-Emitter breakdown voltage	BV_CEO	$I_C=1$ mA, $I_B=0$	160	-	-	V
Emitter-Base breakdown voltage	BV_{EBO}	$I_E = 10 \mu A, I_C = 0$	6	-	-	V
Collector cut-off current	I _{CBO}	V _{CB} =120V, I _E =0	-	-	100	nA
Emitter cut-off current	I _{EBO}	V _{EB} =4V, I _C =0	-	-	100	nA
DC current gain	h _{FE (1)}	$V_{CE}=5V$, $I_{C}=1mA$	80	-		-
DC current gain	h _{FE (2)}	V _{CE} =5V, I _C =10mA	80	-	250	-
DC current gain	h _{FE (3)}	$V_{CE}=5V$, $I_{C}=50mA$	30	-		-
Collector-Emitter saturation voltage	V _{CE(sat)(1)} *	I _C =10mA, I _B =1mA	-	-	0.2	V
Collector-Emitter saturation voltage	V _{CE(sat)(2)} *	I _C =50mA, I _B =5mA	-	-	0.5	V
Base-Emitter saturation voltage	V _{BE(sat)(1)} *	I _C =10mA, I _B =1mA	-	-	1	V
Base-Emitter saturation voltage	V _{BE(sat)(2)*}	I _C =50mA, I _B =5mA	-	-	1	V
Transition frequency	f _T	V _{CE} =10V, I _C =10mA	100	-	400	MHz
Collector output capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz	-	-	6	рF

^{* :} Pulse Tester : Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

Electrical Characteristic Curves

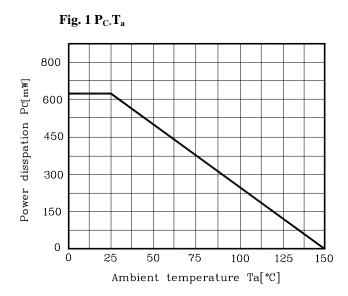


Fig. 3 f_T - I_C

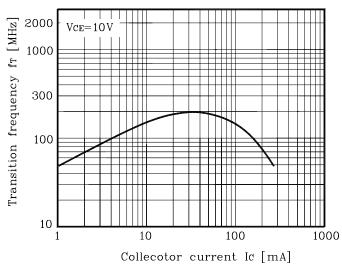


Fig. 5 C_{ob} - V_{CB}

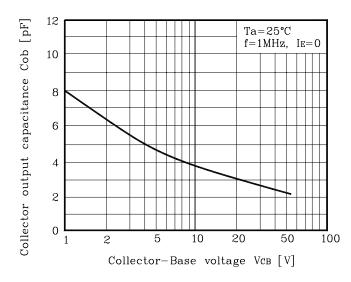


Fig. 2 $I_{\text{C}}\,$ - $\,V_{\text{BE}}$

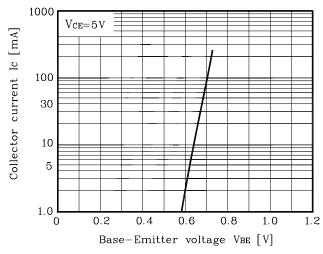
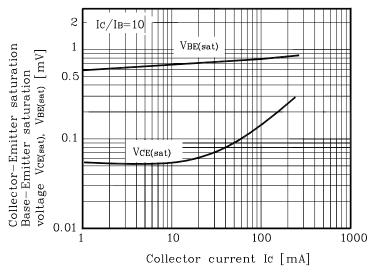
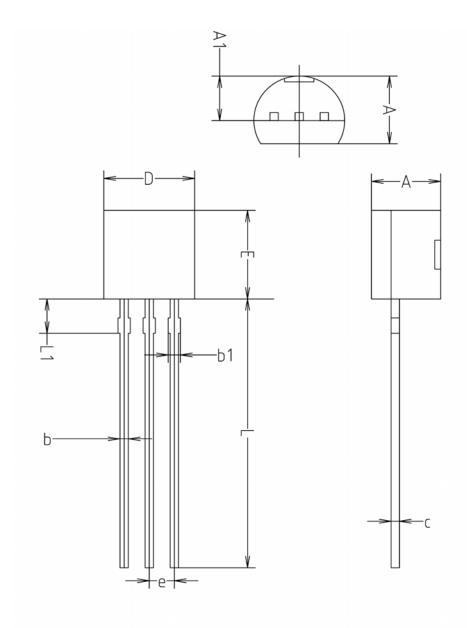


Fig. 4 $V_{CE(sat)}$, $V_{BE(sat)}$ - I_C



KSD-T0A034-000

Outline Dimension



	MILLMETERS(mm)			
SYMBOL	MINIMUM	NOMINAL	MAXIMUM	
Α	3.40	3.50	3.66	
A1	2.46	2.51	2.59	
b	0.39	0.44	0.53	
b1	0.39	-	0.63	
С	0.35	0.42	0.47	
D	4.48	4.60	4.70	
Ε	4.48	4.60	4.70	
е	1.17	1.27	1.37	
L	13.70	14.00	14.77	
L1	1.55	1.70	2.15	

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